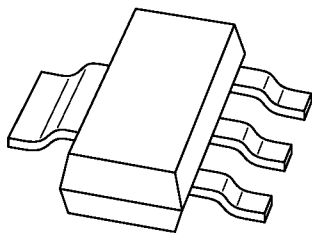


DATA SHEET



BDP31

NPN medium power transistor

Product specification
Supersedes data of 1997 Mar 10

1999 Apr 23

NPN medium power transistor

BDP31

FEATURES

- High current (max. 3 A)
- Low voltage (max. 45 V).

APPLICATIONS

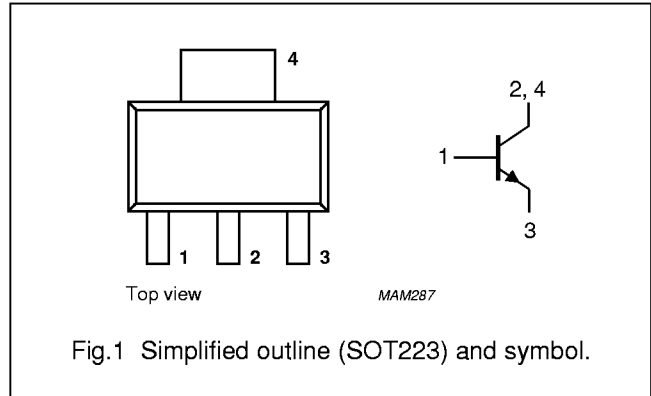
- General purpose medium power applications.

DESCRIPTION

NPN medium power transistor in a SOT223 plastic package. PNP complement: BDP32.

PINNING

PIN	DESCRIPTION
1	base
2,4	collector
3	emitter



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	70	V
V_{CEO}	collector-emitter voltage	open base	–	45	V
V_{EBO}	emitter-base voltage	open collector	–	6	V
I_C	collector current (DC)		–	3	A
I_{CM}	peak collector current		–	6	A
I_{BM}	peak base current		–	0.5	A
P_{tot}	total power dissipation	$T_{mb} \leq 25\text{ °C}$; note 1	–	1.35	W
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		–65	+150	°C

Note

1. Device mounted on a printed-circuit board, single sided copper, tinplated, mounting pad for collector 1 cm². For other mounting conditions, see “Thermal considerations for the SOT223 in the General Part of associated Handbook”.

NPN medium power transistor

BDP31

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	91	K/W
$R_{th\ j-s}$	thermal resistance from junction to soldering point		10	K/W

Note

1. Device mounted on a printed-circuit board, single sided copper, tinplated, mounting pad for collector 1 cm².
For other mounting conditions, see "Thermal considerations for the SOT223 in the General Part of associated Handbook".

CHARACTERISTICS

$T_{amb} = 25\text{ °C}$ unless otherwise specified.

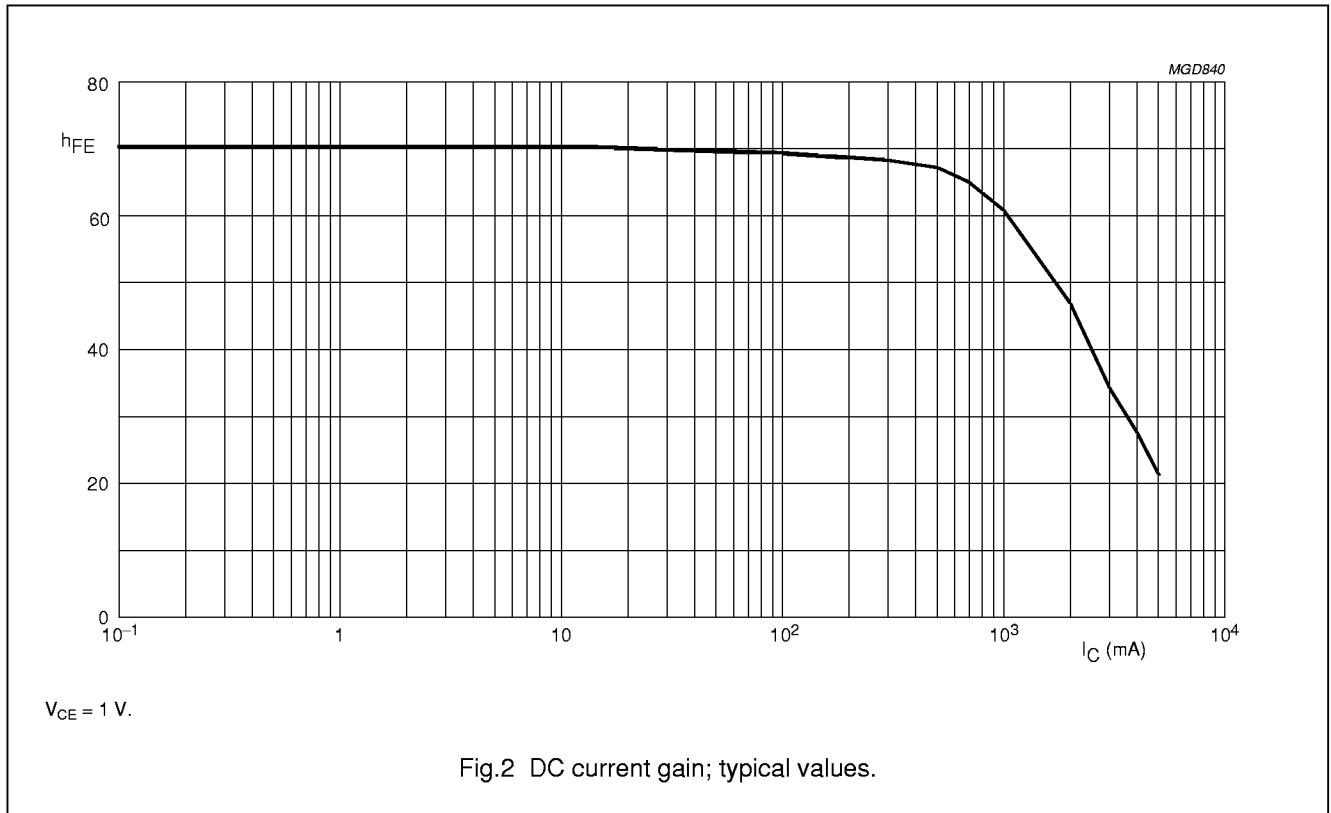
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = 50\text{ V};$	–	50	nA
		$I_E = 0; V_{CB} = 50\text{ V}; T_j = 150\text{ °C}$	–	10	μA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = 5\text{ V};$	–	50	nA
h_{FE}	DC current gain	$I_C = 0.5\text{ A}; V_{CE} = 12\text{ V};$ note 1; see Fig.2	40	–	
		$I_C = 2\text{ A}; V_{CE} = 1\text{ V};$ note 1; see Fig.2	20	–	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 500\text{ mA}; I_B = 50\text{ mA};$ note 1	–	300	mV
		$I_C = 2\text{ A}; I_B = 200\text{ mA};$ note 1	–	700	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = 500\text{ mA}; I_B = 50\text{ mA};$ note 1	–	1.2	V
		$I_C = 2\text{ A}; I_B = 200\text{ mA};$ note 1	–	1.5	V
f_T	transition frequency	$I_C = 250\text{ mA}; V_{CE} = 5\text{ V}; f = 100\text{ MHz}$	60	–	MHz

Note

1. Pulse test: $t_p \leq 300\text{ μs}; \delta \leq 0.02$.

NPN medium power transistor

BDP31



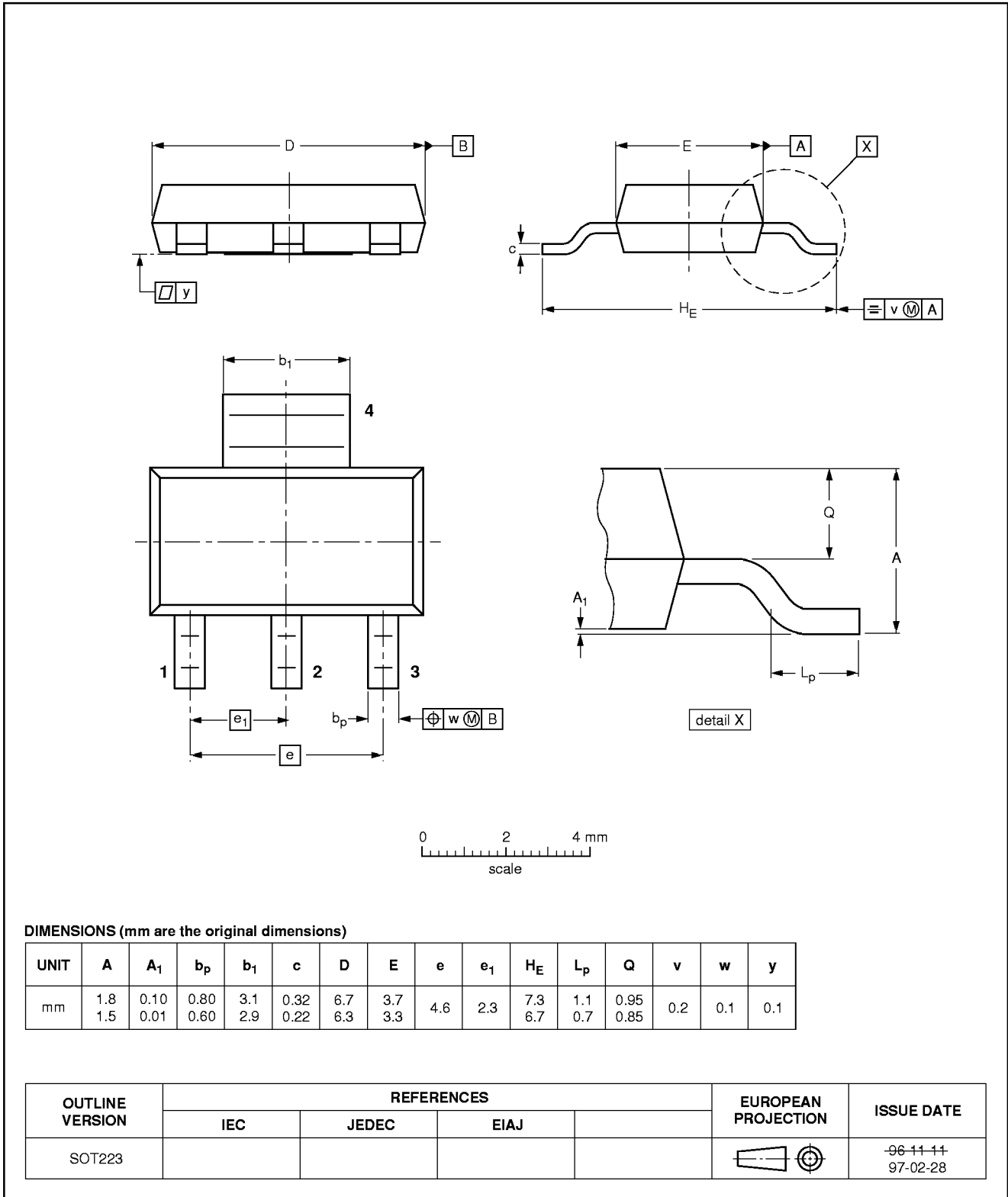
NPN medium power transistor

BDP31

PACKAGE OUTLINE

Plastic surface mounted package; collector pad for good heat transfer; 4 leads

SOT223



NPN medium power transistor

BDP31

DEFINITIONS

Data Sheet Status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.

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